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RECEIVED 19 June 2025  
ACCEPTED 20 June 2025  
PUBLISHED 26 June 2025

CITATION  
Kumar S, Yadav D, Stathopoulos S and  
Prodromakis T (2025) Correction: Performance  
and variability analysis of ALD-grown wafer  
scale HfO<sub>2</sub>/Ta<sub>2</sub>O<sub>5</sub>-based memristive devices  
for neuromorphic computing.  
*Front. Nanotechnol.* 7:1650174.  
doi: 10.3389/fnano.2025.1650174

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# Correction: Performance and variability analysis of ALD-grown wafer scale HfO<sub>2</sub>/Ta<sub>2</sub>O<sub>5</sub>-based memristive devices for neuromorphic computing

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## KEYWORDS

memristive devices, oxide materials, performance matrix, atomic layer deposition, variability factor, device stability

## A Correction on Performance and variability analysis of ALD-grown wafer scale HfO<sub>2</sub>/Ta<sub>2</sub>O<sub>5</sub>-based memristive devices for neuromorphic computing

by Kumar S, Yadav D, Stathopoulos S and Prodromakis T (2025). *Front. Nanotechnol.* 7:1621554.  
doi: 10.3389/fnano.2025.1621554

**Affiliations** 1 and 2 were numbered incorrectly as <sup>1</sup>Department of Electronics Engineering, Indian Institute of Technology (ISM), Dhanbad, Jharkhand, India, <sup>2</sup>School of Engineering, Centre for Electronics Frontiers, Integrated Micro and Nano Systems, The University of Edinburgh, Edinburgh, Scotland, United Kingdom. The correct affiliations appear above. The original version of this article has been updated.

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